

DATA SHEET

BSN254

BSN254A

N-channel enhancement mode
vertical D-MOS transistors

Product specification
File under Discrete Semiconductors, SC13b

April 1995

**N-channel enhancement mode vertical
D-MOS transistors**

**BSN254
BSN254A**

DESCRIPTION	QUICK REFERENCE DATA			
N-channel enhancement mode vertical D-MOS transistors in TO-92 variant envelope and designed for use as line current interrupters in telephone sets and for application in relay, high-speed and line-transformer drivers.	Drain-source voltage	V_{DS}	max.	250 V
	Drain current (DC)	I_D	max.	300 mA
	Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot}	max.	1 W
	Drain-source on-resistance $I_D = 300\text{ mA}; V_{GS} = 10\text{ V}$	$R_{DS(on)}$	typ. max.	5.0 Ω 7.0 Ω
	Gate-source threshold voltage	$V_{GS(th)}$	max.	2 V

FEATURES

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No second breakdown
- Low $R_{DS(on)}$

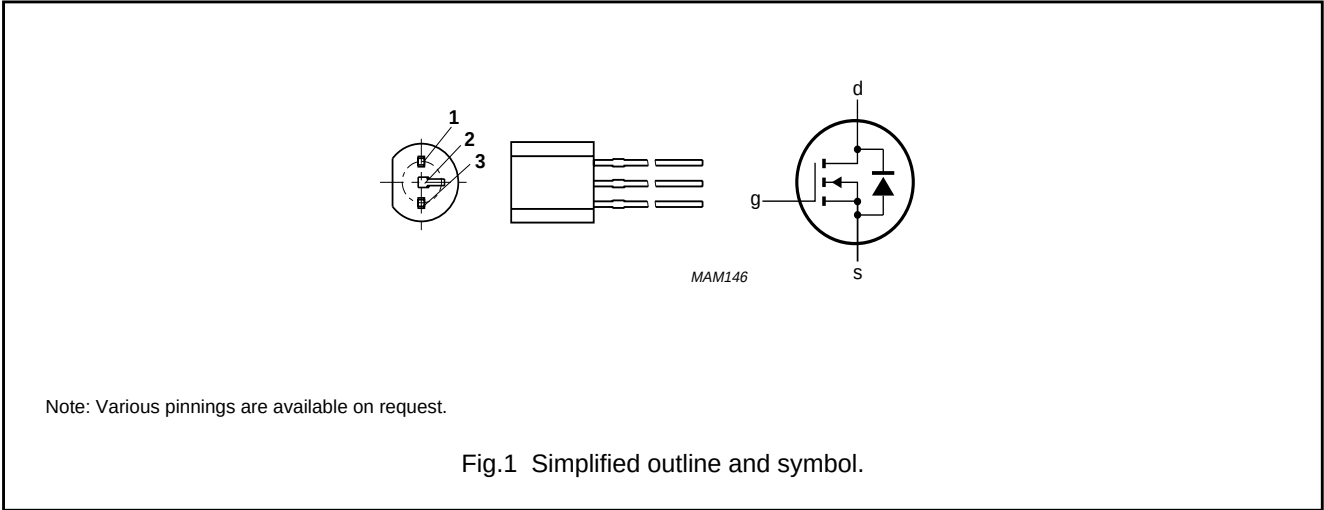
PINNING (BSN254)

- 1 = gate
- 2 = drain
- 3 = source

PINNING (BSN254A)

- 1 = source
- 2 = gate
- 3 = drain

PIN CONFIGURATION - TO-92 VARIANT



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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	250 V
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20 V
Drain current (DC)	I_D	max.	300 mA
Drain current (peak)	I_{DM}	max.	1.2 A
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$ (note 1)	P_{tot}	max.	1 W
Storage temperature range	T_{stg}	–65 to + 150	$^{\circ}\text{C}$
Junction temperature	T_j	max.	150 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient (note 1)	$R_{th\ j-a}$	=	125 K/W
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Note

1. Device mounted on printed-circuit board, max. lead length 4 mm, mounting pad for drain lead min. 10 mm × 10 mm.

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Drain-source breakdown voltage $I_D = 10\text{ }\mu\text{A}$; $V_{GS} = 0$	$V_{(BR)\ DSS}$	min.	250 V
Drain-source leakage current $V_{DS} = 200\text{ V}$; $V_{GS} = 0$	I_{DSS}	max.	1 μA
Gate-source leakage current $\pm V_{GS} = 20\text{ V}$; $V_{DS} = 0$	$\pm I_{GSS}$	max.	100 nA
Gate threshold voltage $I_D = 1\text{ mA}$; $V_{DS} = V_{GS}$	$V_{GS(th)}$	min. max.	0.8 V 2.0 V
Drain-source on-resistance $I_D = 300\text{ mA}$; $V_{GS} = 10\text{ V}$	$R_{DS(on)}$	typ. max.	5.0 Ω 7.0 Ω
$I_D = 20\text{ mA}$; $V_{GS} = 2.4\text{ V}$	$R_{DS(on)}$	max.	10 Ω
Transfer admittance $I_D = 300\text{ mA}$; $V_{DS} = 25\text{ V}$	$ Y_{fs} $	min. typ.	200 mS 400 mS
Input capacitance at $f = 1\text{ MHz}$ $V_{DS} = 25\text{ V}$; $V_{GS} = 0$	C_{iss}	typ. max.	65 pF 90 pF

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Output capacitance at $f = 1\text{ MHz}$

$V_{DS} = 25\text{ V}; V_{GS} = 0$

C_{oss}	typ.	20 pF
	max.	30 pF

Feedback capacitance at $f = 1\text{ MHz}$

$V_{DS} = 25\text{ V}; V_{GS} = 0$

C_{rss}	typ.	5 pF
	max.	15 pF

Switching times (see Figs 2 and 3)

$I_D = 250\text{ mA}; V_{DD} = 50\text{ V}; V_{GS} = 0\text{ to }10\text{ V}$

t_{on}	typ.	5 ns
	max.	10 ns
t_{off}	typ.	20 ns
	max.	30 ns

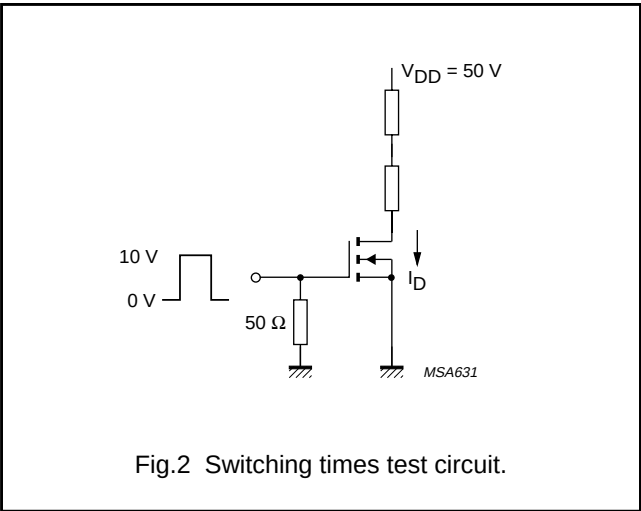


Fig.2 Switching times test circuit.

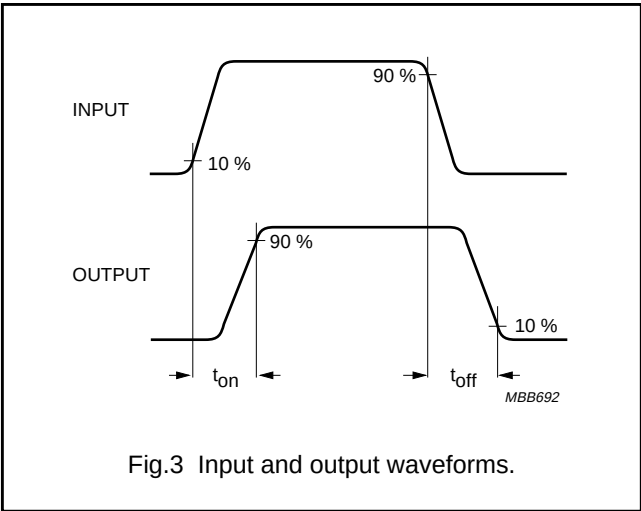


Fig.3 Input and output waveforms.

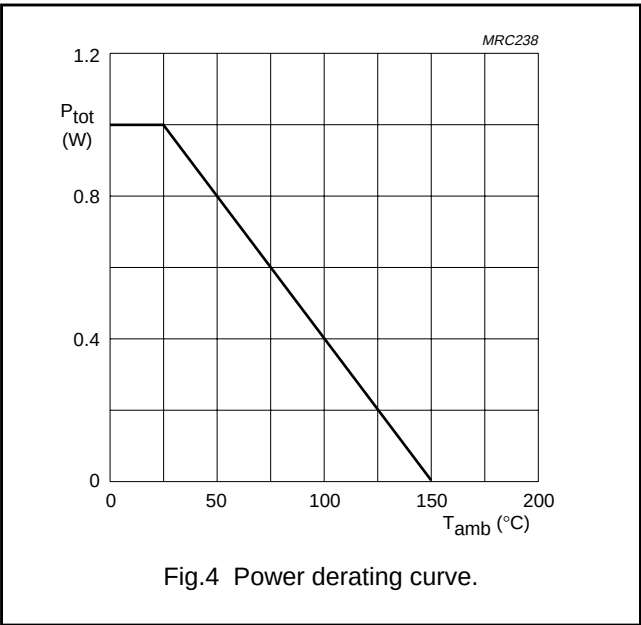


Fig.4 Power derating curve.

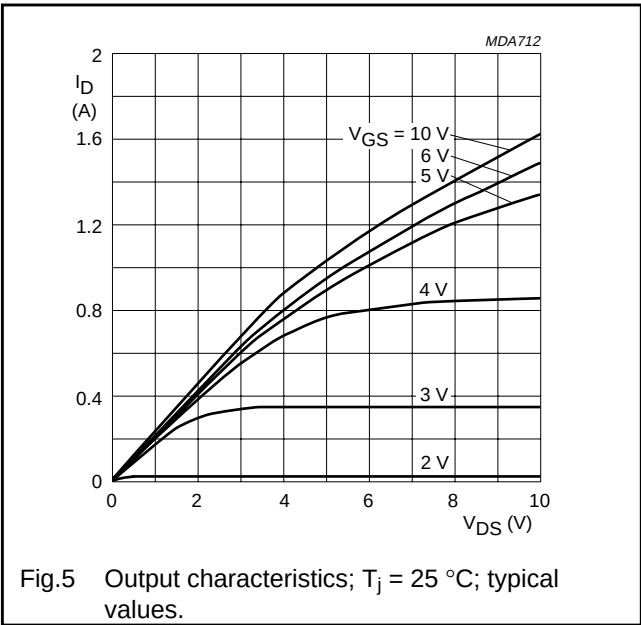


Fig.5 Output characteristics; T_j = 25 °C; typical values.

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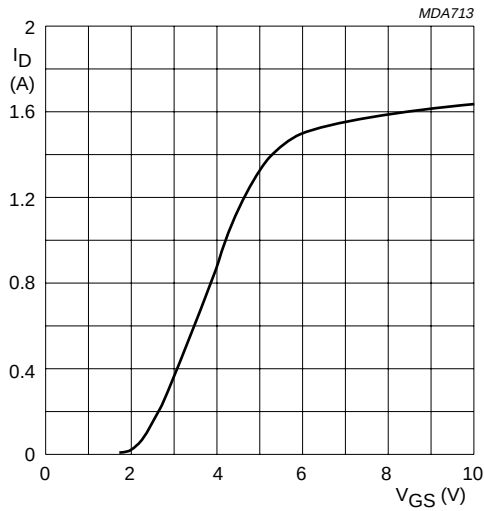


Fig. 6 Transfer characteristic; $V_{DS} = 10\text{ V}$;
 $T_j = 25\text{ }^\circ\text{C}$; typical value.

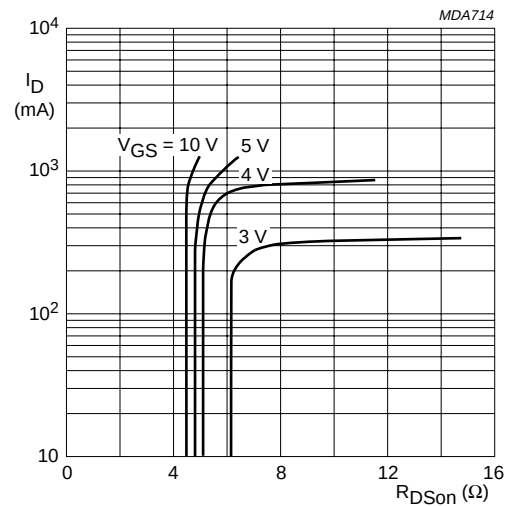


Fig. 7 On-resistance as a function of drain current;
 $T_j = 25\text{ }^\circ\text{C}$; typical values.

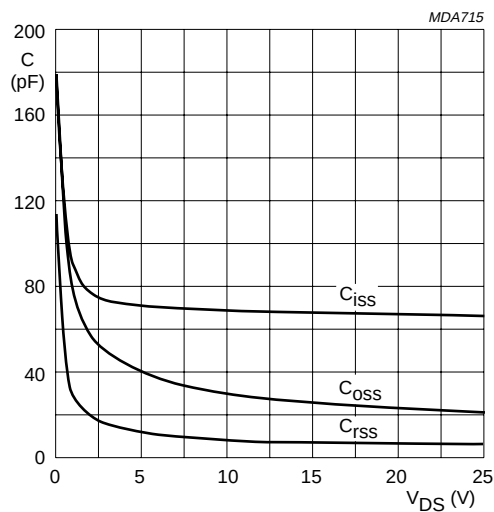


Fig. 8 Capacitances as a function of drain-source
voltage; $V_{GS} = 0$; $f = 1\text{ MHz}$; $T_j = 25\text{ }^\circ\text{C}$;
typical values.

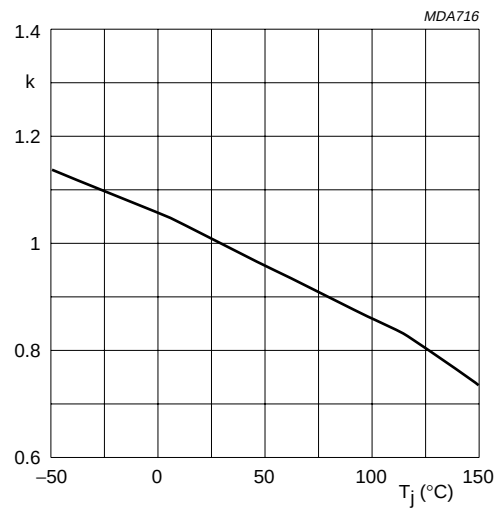


Fig. 9

$$k = \frac{V_{GS(th)} \text{ at } T_j}{V_{GS(th)} \text{ at } 25\text{ }^\circ\text{C}};$$

$V_{GS(th)}$ at 1 mA; typical values

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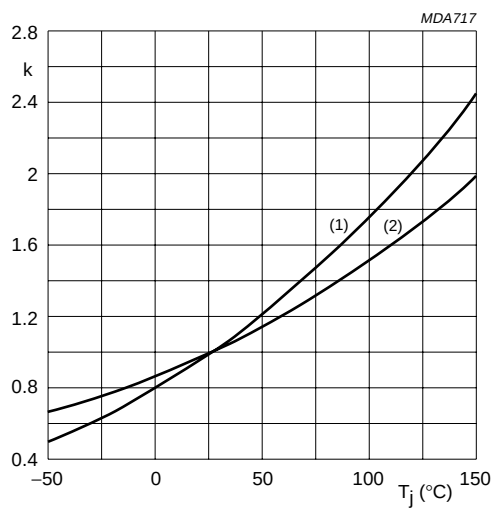


Fig.10

$$k = \frac{R_{DS(on)} \text{ at } T_j}{R_{DS(on)} \text{ at } 25^\circ\text{C}};$$

typical values.

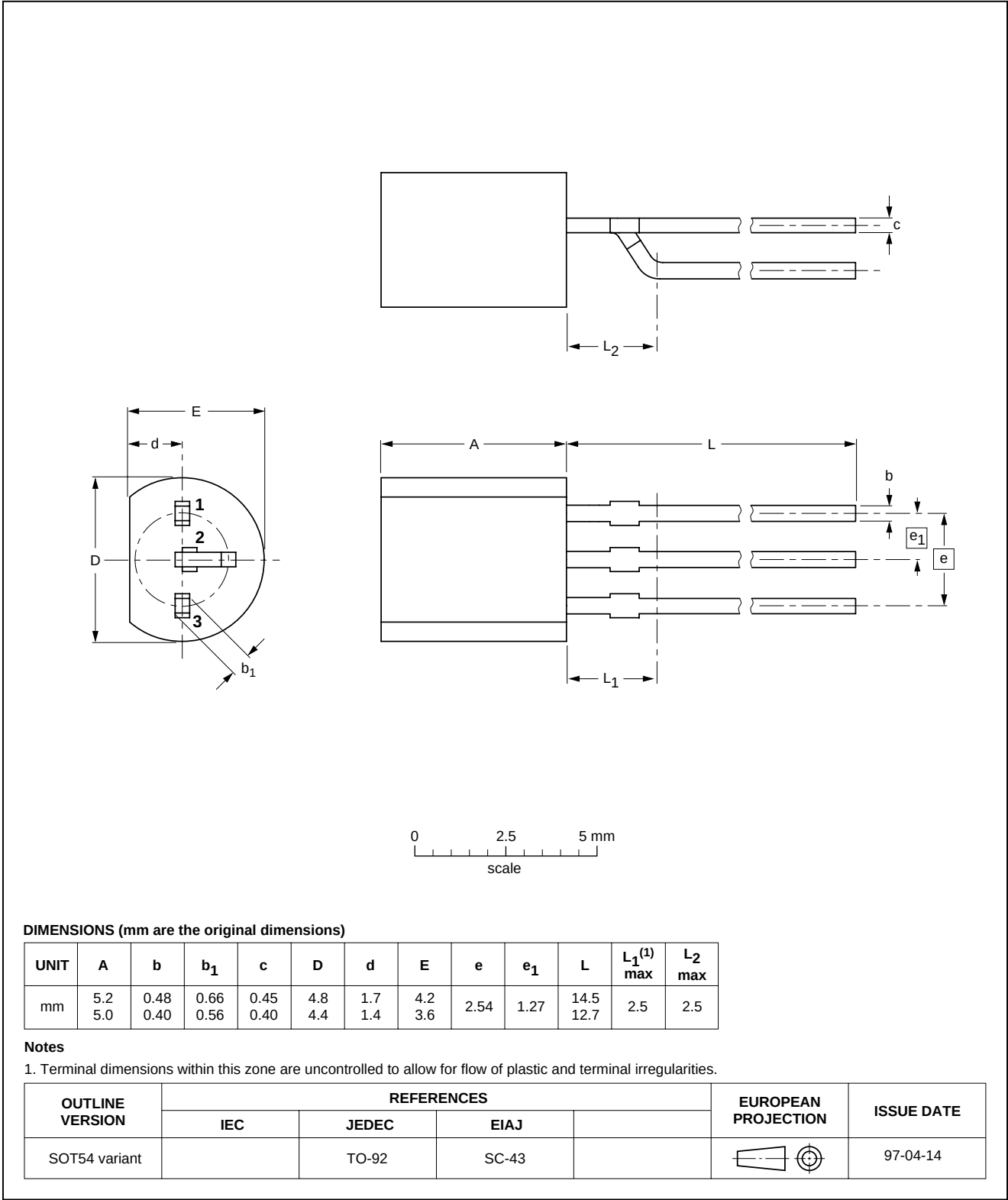
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PACKAGE OUTLINES

Plastic single-ended leaded (through hole) package; 3 leads (on-circle)

SOT54 variant



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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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NOTES

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